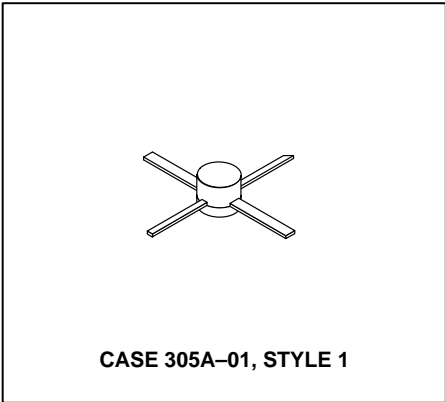


The RF Line
NPN Silicon
High-Frequency Transistor

... designed for wideband amplifier, driver or oscillator applications in military, mobile, and aircraft radio.

- Specified 28 Volt, 400 MHz Characteristics —
Output Power = 1.0 Watt
Power Gain = 15 dB Min
Efficiency = 45% Typ
- Emitter Ballast and Low Current Density for Improved MTBF
- Common Emitter for Improved Stability



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	30	Vdc
Collector–Base Voltage	V _{CB0}	40	Vdc
Emitter–Base Voltage	V _{EBO}	3.0	Vdc
Collector Current — Continuous	I _C	150	mAdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	6.1 35	Watts mW/°C
Storage Temperature Range	T _{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	28.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	30	—	—	Vdc
Collector–Emitter Breakdown Voltage (I _C = 5.0 mAdc, V _{BE} = 0)	V _{(BR)CES}	35	—	—	Vdc
Collector–Base Breakdown Voltage (I _C = 0.1 mAdc, I _E = 0)	V _{(BR)CBO}	35	—	—	Vdc
Emitter–Base Breakdown Voltage (I _E = 1.0 mAdc, I _C = 0)	V _{(BR)EBO}	3.0	—	—	Vdc
Collector Cutoff Current (V _{CE} = 20 Vdc, I _B = 0)	I _{CEO}	—	—	1.0	mAdc

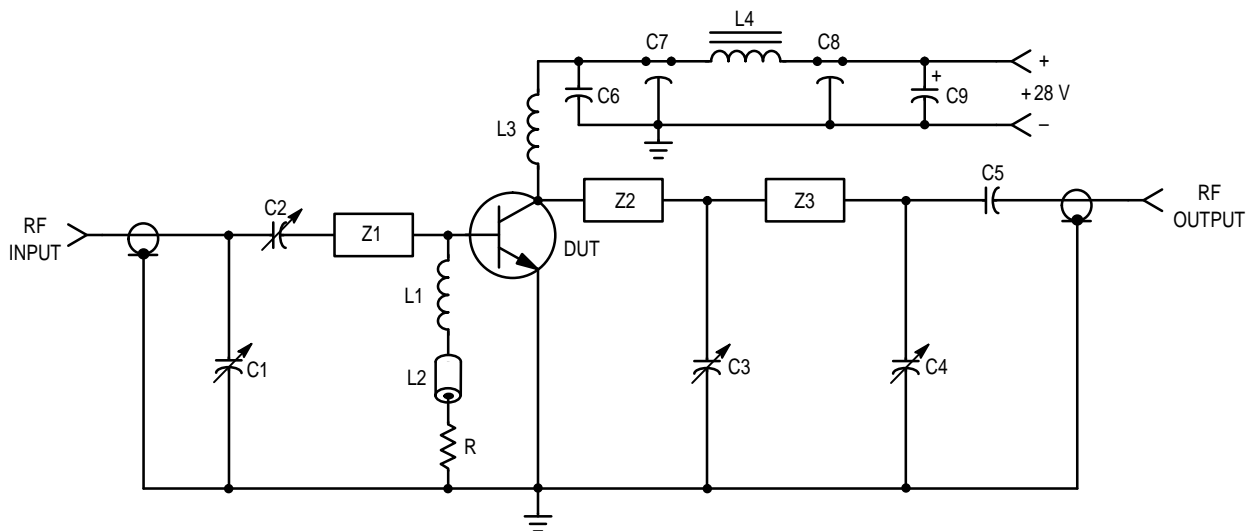
(continued)

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100 \text{ mA dc}$, $V_{CE} = 10 \text{ V dc}$)	h_{FE}	20	60	150	—
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product ($I_C = 100 \text{ mA dc}$, $V_{CE} = 20 \text{ V dc}$, $f = 200 \text{ MHz}$)	f_T	—	2.5	—	GHz
Output Capacitance ($V_{CB} = 28 \text{ V dc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	3.5	5.0	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (1) ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	G_{pe}	15	16	—	dB
Collector Efficiency ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	η	—	45	—	%
Series Equivalent Input Impedance ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	Z_{in}	—	$6.4 - j4.8$	—	Ohms
Series Equivalent Output Impedance ($V_{CC} = 28 \text{ V dc}$, $P_{out} = 1.0 \text{ W}$, $f = 400 \text{ MHz}$)	Z_{out}	—	$75 - j45$	—	Ohms

NOTE:

- Class C



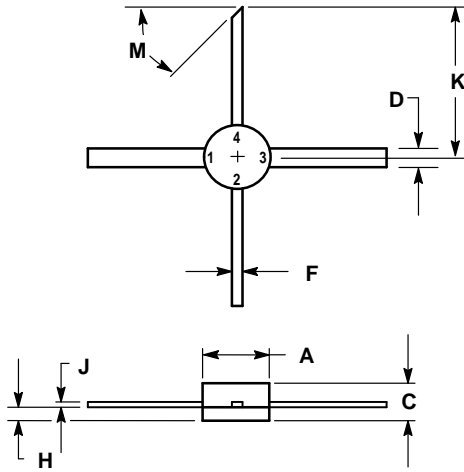
C1, C2, C4 — 1.0–20 pF JOHANSON 9063
 C3 — 1.0–10 pF JOHANSON
 C5 — 150 pF Chip
 C6 — 0.1 μF
 C7, C8 — 680 pF Feedthru
 C9 — 1.0 μF TANTALUM

L1, L3 — 5 Turns, AWG #20, 1/4" I.D.
 L2 — Ferrite Bead, FERROXCUBE
 No. 56–590–65/4B
 L4 — FERROXCUBE VK200–20/4B
 Input/Output Connectors — Type N
 Board — Glass Teflon, $\epsilon = 2.56$, $t = 0.062$ "

R — 4.7 Ohms, 1/4 W
 Z1 — 2.0" x 0.1" MICROSTRIP LINE
 Z2, Z3 — 2.6" x 0.1" MICROSTRIP LINE

Figure 1. 400 MHz Power Gain Test Circuit

PACKAGE DIMENSIONS




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.200	0.220	5.08	5.59
C	0.095	0.130	2.41	3.30
D	0.055	0.065	1.40	1.65
F	0.025	0.035	0.64	0.89
H	0.040	0.050	1.02	1.27
J	0.003	0.007	0.08	0.18
K	0.435	—	11.05	—
M	45 °REF		45 °REF	

- STYLE 1:
 PIN 1. EMITTER
 2. BASE
 3. EMITTER
 4. COLLECTOR

**CASE 305A-01
 ISSUE A**

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